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(71) Applicant: **IGSS-GAN PTE LTD** [SG/SG]; Mewah Building, #02-07A, 5 International Business Park, 609914 (SG).

(72) Inventors: **ONG, Kian Keong**; Mewah Building, #02-07A, 5 International Business Park, 609914 (SG).
GAO, Yuan; Mewah Building, #02-07A, 5 International Business Park, 609914 (SG).

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(54) Title: SEMICONDUCTOR APPARATUS AND METHOD FOR FABRICATING THEREOF

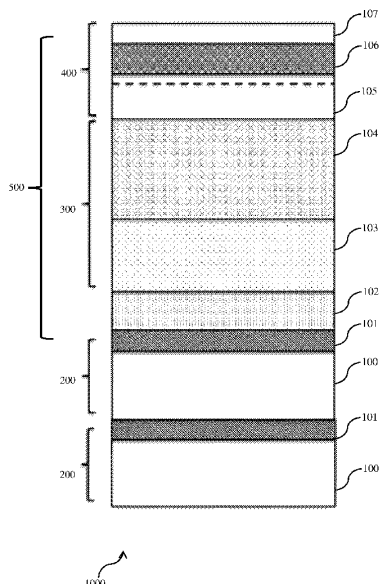


Figure 1

(57) Abstract: The present invention relates to a method (700) for fabricating a semiconductor apparatus. The method (700) includes providing a surface engineered nitride (SEN) template (702) and forming a III-nitride semiconductor device stack on the SEN template (704). The III-nitride semiconductor device stack comprises an Aluminum nitride (AlN) layer, a buffer structure and a device structure.